

# BUK7880-55A

# N-channel TrenchMOS standard level FET

19 June 2015

**Product data sheet** 

### 1. General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using Nexperia General Purpose Automotive (GPA) TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

#### 2. Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- · Suitable for standard level gate drive sources

### 3. Applications

- 12 V and 24 V loads
- Automotive systems
- General purpose power switching
- · Motors, lamps and solenoids

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 150 °C		-	-	55	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>sp</sub> = 25 °C; <u>Fig. 2</u> ; <u>Fig. 3</u>		-	-	7	Α
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 25 °C; <u>Fig. 1</u>		-	-	8	W
Static characte	Static characteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 10 A; $T_j$ = 25 °C; Fig. 9; Fig. 10		-	68	80	mΩ
Avalanche rug	Avalanche ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$I_D$ = 7 A; $V_{sup} \le 55$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	-	53	mJ



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### 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	4	D I
2	D	drain		
3	S	source		G T T
4	D	drain	⊟1 ⊟2 ⊟3 SC-73 (SOT223)	mbb076 S

### 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BUK7880-55A	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223			
BUK7880-55A/CU	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223			

## 7. Marking

Table 4. Marking codes

Type number	Marking code
BUK7880-55A	788055A
BUK7880-55A/CU	788055

# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

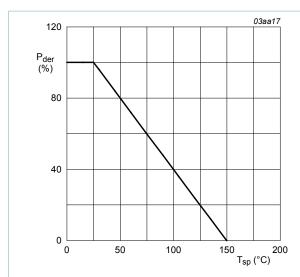
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 150 °C	-	55	V
$V_{DGR}$	drain-gate voltage	$R_{GS}$ = 20 k $\Omega$	-	55	V
$V_{GS}$	gate-source voltage		-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 25 °C; <u>Fig. 1</u>	-	8	W
I <sub>D</sub>	drain current	T <sub>sp</sub> = 100 °C; V <sub>GS</sub> = 10 V; <u>Fig. 2</u>	-	5	Α
		T <sub>sp</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	7	Α
I <sub>DM</sub>	peak drain current	$T_{sp}$ = 25 °C; pulsed; $t_p \le 10 \mu s$ ; Fig. 3	-	30	А

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Symbol	Parameter	Conditions		Min	Max	Unit
T <sub>stg</sub>	storage temperature			-55	150	°C
T <sub>j</sub>	junction temperature			-55	150	°C
Source-drain	diode					
Is	source current	T <sub>sp</sub> = 25 °C		-	7	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{sp} = 25 \ ^{\circ}C$		-	30	Α
Avalanche ru	iggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 7 A; $V_{sup} \le 55$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	53	mJ
E <sub>DS(AL)R</sub>	repetitive drain-source avalanche energy	Fig. 4	[1][2][3]	[4 <del>]</del>	-	J

- Maximum value not quoted. Repetitive rating defined in avalanche rating figure. Single-pulse avalanche rating limited by maximum junction temperature of 150  $^{\circ}$ C. [2]
- [3] Repetitive avalanche rating limited by an average junction temperature of 150 °C
- Refer to application note AN10273 for further information. [4]



Normalized total power dissipation as a function of solder point temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

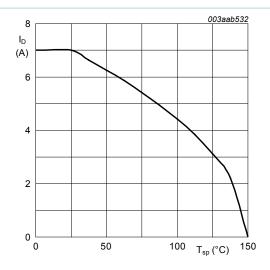


Fig. 2. Continuous drain current as a function of solder point temperature

$$V_{\rm GS} \ge 10~V$$

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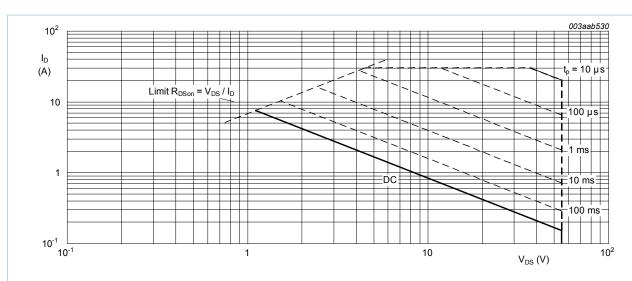
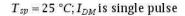


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



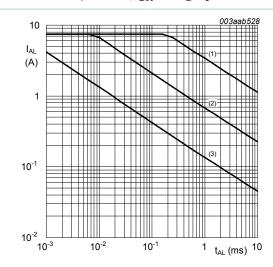


Fig. 4. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time

#### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-	-	15	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient		-	120	-	K/W

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### 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 ^{\circ}C$	55	-	-	V
breakdown voltage		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	50	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}; Fig. 8$	2	3	4	V
V <sub>GSth</sub> gate-source threshold voltage		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 8	-	-	4.4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C};$ Fig. 8	1.2	-	-	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 55 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.05	10	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
200	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 150 °C; Fig. 9; Fig. 10	-	-	148	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 25 °C; Fig. 9; Fig. 10	-	68	80	mΩ
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 55 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	500	μA
Dynamic o	characteristics					
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 10 A; V <sub>DS</sub> = 44 V; V <sub>GS</sub> = 10 V;	-	12	-	nC
$Q_{GS}$	gate-source charge	Fig. 11	-	2.5	-	nC
$Q_{GD}$	gate-drain charge		-	5	-	nC
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz;	-	374	500	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 12</u>	-	92	110	pF
C <sub>rss</sub>	reverse transfer capacitance		-	62	85	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$	-	8	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 10 \Omega$	-	52	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	17	-	ns
t <sub>f</sub>	fall time		-	9	-	ns
Source-dr	ain diode					
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 15 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <u>Fig. 13</u>	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	_	33	_	ns
4T	reverse receivery anne	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}$				

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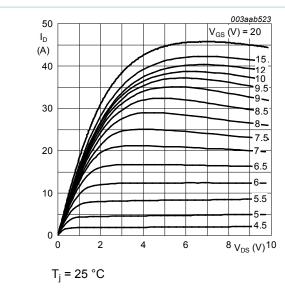


Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values

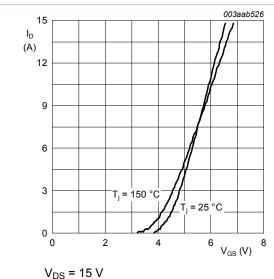
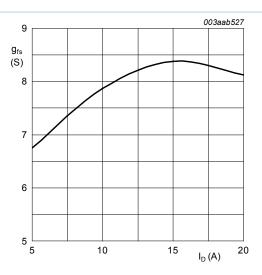


Fig. 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $T_j$  = 25 °C;  $V_{DS}$  = 15 V

Fig. 6. Forward transconductance as a function of drain current; typical values

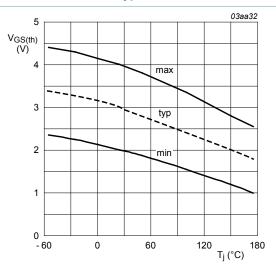


Fig. 8. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1mA; V_{DS} = V_{GS}$$

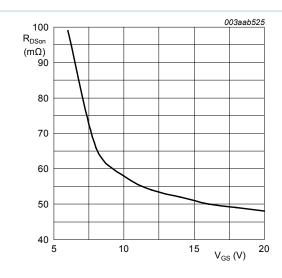


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25 \,{}^{\circ}C; I_D = 10 \, A$$

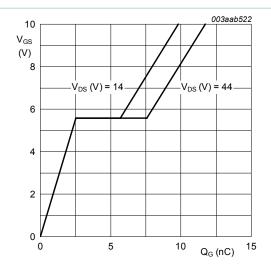


Fig. 11. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25\,^{\circ}C; I_D = 10A$$

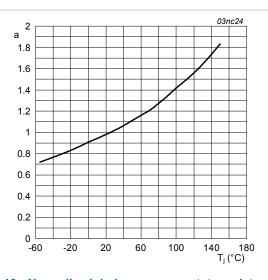


Fig. 10. Normalized drain source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

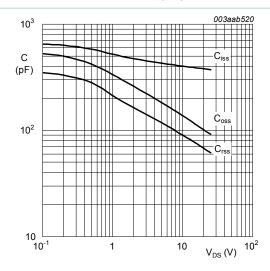


Fig. 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V; f = 1MHz$$

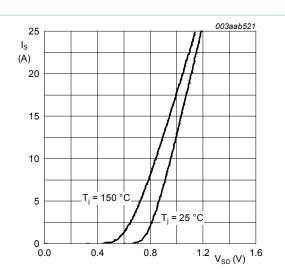
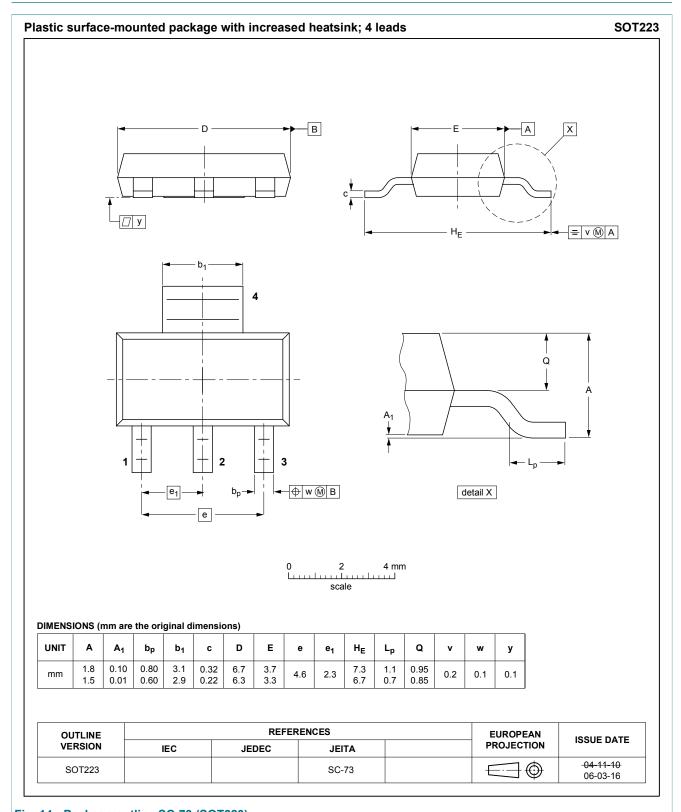


Fig. 13. Source current as a function of source-drain voltage; typical values

$$V_{GS} = \mathbf{0}V$$

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### 11. Package outline



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